

TECHNICAL DATA
DATA SHEET 4675, REV. -**HERMETIC POWER SCHOTTKY RECTIFIER**
Low Forward Voltage**Applications:**

· Switching Power Supply · Converters · Free-Wheeling Diodes · Polarity Protection Diode

Features:

- Soft Reverse Recovery at Low and High Temperature
- Low Forward Voltage Drop
- Low Power Loss, High Efficiency
- High Surge Capacity
- Guard Ring for Enhanced Durability and Long Term Reliability
- Guaranteed Reverse Avalanche Characteristics

Maximum Ratings:

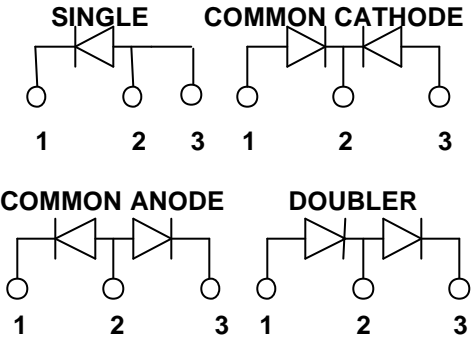
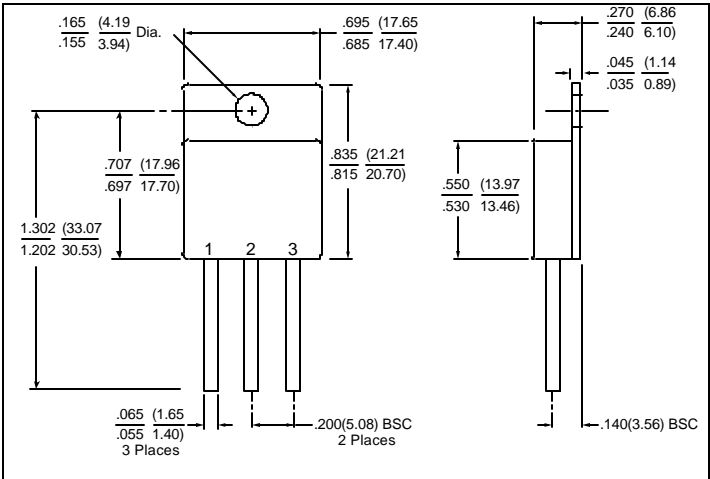
Characteristics	Symbol	Condition	Max.	Units
Peak Inverse Voltage	V_{RWM}	-	200	V
Max. Average Forward Current	$I_{F(AV)}$	50% duty cycle, rectangular wave form (Single/Doubler)	7.5	A
Max. Average Forward Current	$I_{F(AV)}$	50% duty cycle, rectangular wave form (Common Cathode/Common Anode)	15	A
Max. Peak One Cycle Non-Repetitive Surge Current	I_{FSM}	8.3 ms, half Sine wave (per leg)	140	A
Max. Thermal Resistance	$R_{\theta JC}$	(Single)	1.36	°C/W
Max. Junction Temperature	T_J	-	-65 to +200	°C
Max. Storage Temperature	T_{stg}	-	-65 to +200	°C

Electrical Characteristics:

Characteristics	Symbol	Condition	Max.	Units
Max. Forward Voltage Drop	V_{F1}	@ 7.5A, Pulse, $T_J = 25\text{ }^{\circ}\text{C}$ (per leg)	1.01	V
	V_{F2}	@ 7.5A, Pulse, $T_J = 125\text{ }^{\circ}\text{C}$ (per leg)	0.85	V
Max. Reverse Current	I_{R1}	@ $V_R = 200\text{V}$, Pulse, $T_J = 25\text{ }^{\circ}\text{C}$ (per leg)	0.008	μA
	I_{R2}	@ $V_R = 200\text{V}$, Pulse, $T_J = 125\text{ }^{\circ}\text{C}$ (per leg)	0.5	mA
Max. Junction Capacitance	C_T	@ $V_R = 5\text{V}$, $T_C = 25\text{ }^{\circ}\text{C}$ $f_{SIG} = 1\text{MHz}$, $V_{SIG} = 50\text{mV}$ (p-p) (per leg)	150	pF

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Mechanical Dimensions: In Inches / mm

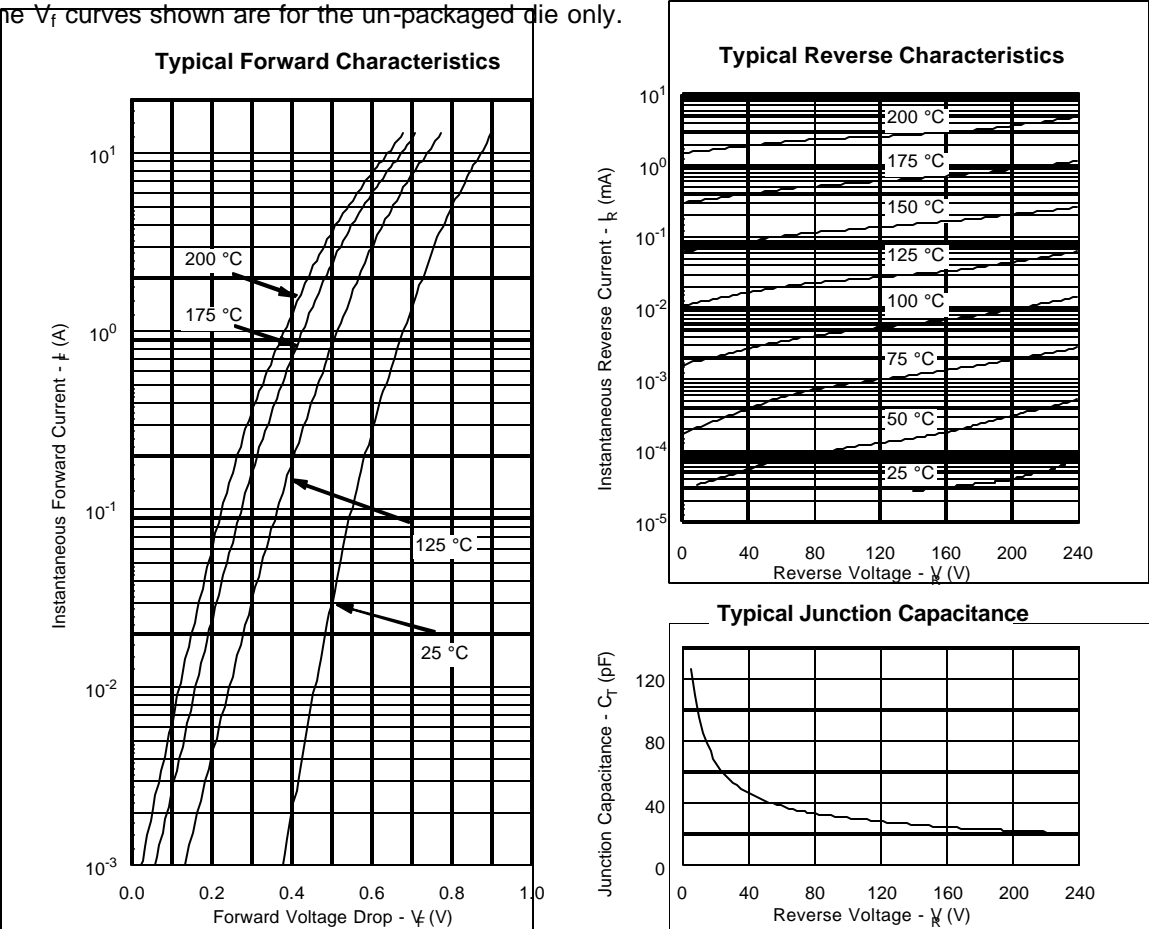


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PINOUT TABLE

TYPE	PIN 1	PIN 2	PIN 3
SINGLE RECTIFIER	CATHODE	ANODE	ANODE
DUAL RECTIFIER, COMMON CATHODE (P)	ANODE 1	COMMON CATHODE	ANODE 2
DUAL RECTIFIER, COMMON ANODE (N)	CATHODE 1	COMMON ANODE	CATHODE 2
DUAL RECTIFIER, DOUBLER (D)	ANODE	CATHODE/ANODE	CATHODE

Note: The V_f curves shown are for the un-packaged die only.



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